## NSN 5961-01-171-3726

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Inclosure Material:



View Online at https://aerobasegroup.com/nsn/5961-01-171-3726

Metal
Overall Length:
1.563 inches
Overall Height:
0.350 inches
Overall Width:
1.050 inches
Mounting Facility Quantity:
2
nternal Configuration:
Junction contact-darlington connected
Joint Electronic Device Engineering Council/jedec/case Outline Designation:
Го-3
Electrode Internally-electrically Connected To Case:
Collector
Mounting Method:
Unthreaded hole
Features Provided:
Hermetically sealed case
Semiconductor Material:
Silicon
Voltage Rating In Volts Per Characteristic:
30.0 collector to emitter voltage/static/base open and 80.0 collector to base voltage, dc and 5.0 emitter to base voltage, dc
Current Rating Per Characteristic:
10.00 amperes source cutoff current and 200.00 milliamperes source cutoff current
Power Rating Per Characteristic:
100.0 watts small-signal input power, common-collector preset
Transfer Ratio:
4.0 static forward current transfer ratio, common-emitter
Maximum Operating Tempurature Per Measurement Point:
200.0 degrees celsius junction
Special Features:
Junction pattern arrangement: npn
Test Data Document:
30003-911as8129 drawing (this is the basic governing drawing, such as a contractor drawing, original equipment manufacturer drawing,
etc.; excludes any specification, standard or other document that may be referenced in a basic governing drawing)
Terminal Type And Quantity:
2 uninsulated wire lead and 1 case
Shelf Life:
N/a
Unit Of Measure:

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Demilitarization:

No

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